

Abstract Submitted
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Kondo physics with ac driving in the single electron transistor subjected to finite bias ALI GOKER, Universite de Montreal — We employ the time-dependent non-crossing approximation to study the time averaged conductance for a single electron transistor in the Kondo regime when the dot level is sinusoidally driven from its equilibrium position by means of a gate voltage in finite bias. We find that the average conductance exhibits considerable deviation from the monotonous reduction when the applied bias is equal to the driving frequency of the dot level. We attribute this behaviour to the overlap of the satellite Kondo peaks with the split Kondo resonances formed at each lead's Fermi level. We display the spectral function to put our interpretation into more rigorous footing. We also investigate the effect of the temperature and the driving frequency on the observed enhancement.

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